

DATA SHEET

BLV935 UHF power transistor

Product specification

1995 Jun 29

UHF power transistor

BLV935

FEATURES

- Emitter ballasting resistors for an optimum temperature profile
- Gold metallization ensures excellent reliability
- Internal input matching to achieve high power gain and easy design of wideband circuits.

APPLICATIONS

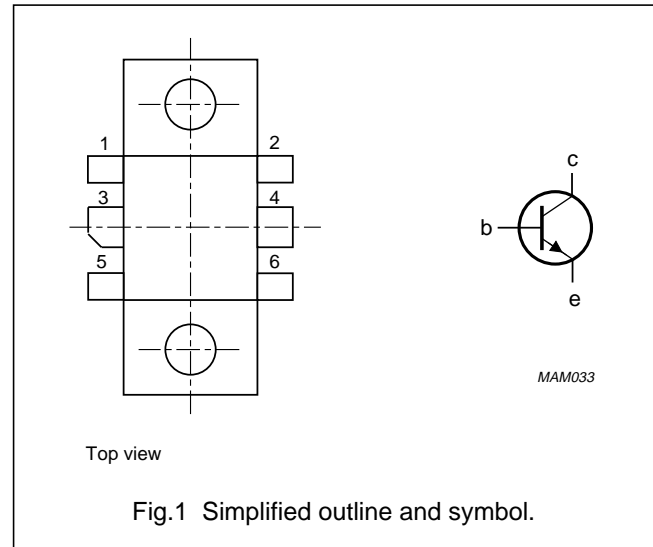
- Base stations in the 820 to 980 MHz range.

PINNING - SOT273

PIN	SYMBOL	DESCRIPTION
1	e	emitter
2	e	emitter
3	c	collector
4	b	base
5	e	emitter
6	e	emitter

DESCRIPTION

NPN silicon planar epitaxial transistor intended for common emitter class-AB operation. The transistor has internal input matching by means of MOS capacitors and is encapsulated in a 6-lead SOT273 flange envelope with a ceramic cap. All leads are isolated from the flange.



QUICK REFERENCE DATA

RF performance at $T_h = 25\text{ °C}$ in a common emitter test circuit.

MODE OF OPERATION	f (MHz)	V_{CE} (V)	P_L (W)	G_p (dB)	η_c (%)
CW, class-AB	960	26	30	≥ 9	≥ 55

WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

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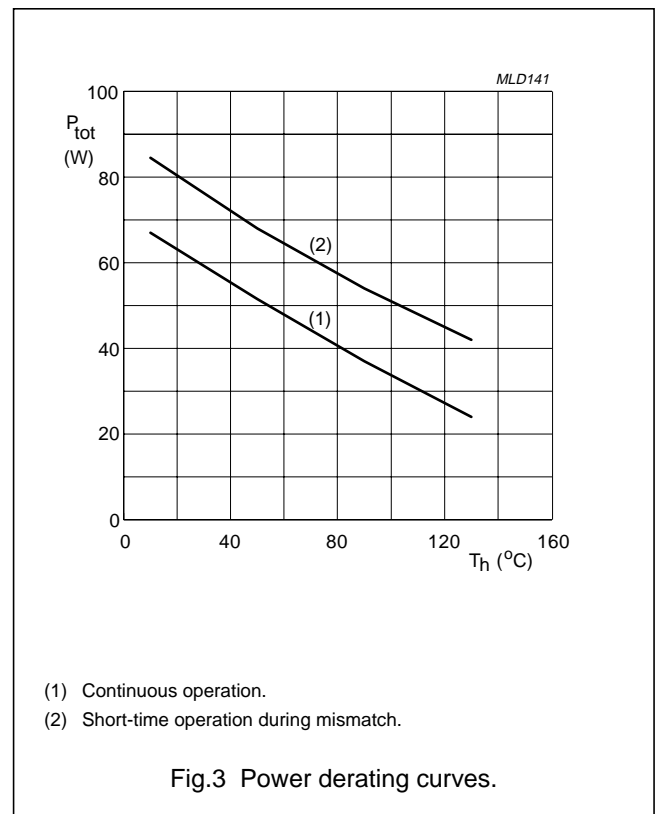
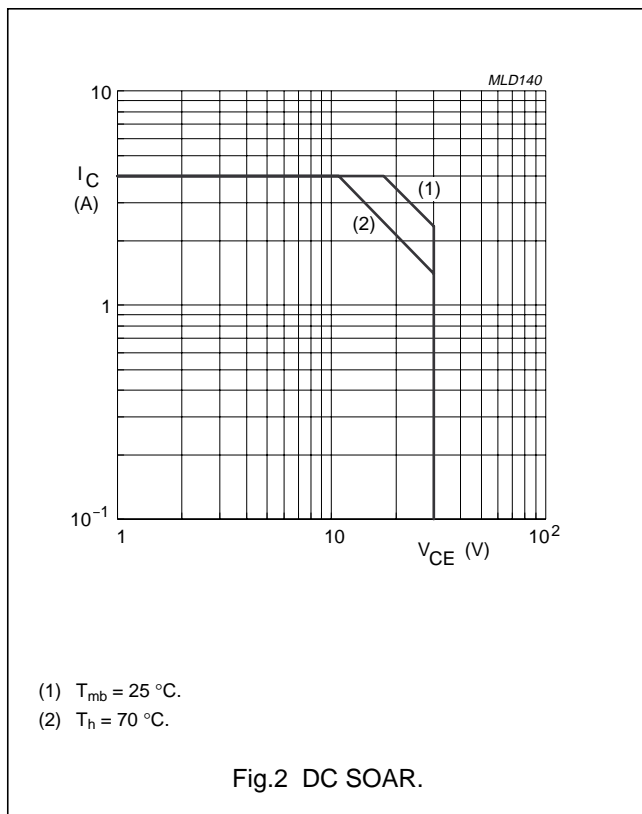
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	70	V
V_{CEO}	collector-emitter voltage	open base	–	30	V
V_{EBO}	emitter-base voltage	open collector	–	3	V
I_C	collector current (DC)		–	4	A
$I_{C(AV)}$	average collector current		–	4	A
P_{tot}	total power dissipation	up to $T_{mb} = 25\text{ °C}$	–	70	W
T_{stg}	storage temperature		–65	+150	°C
T_j	operating junction temperature		–	+200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$P_{tot} = 70\text{ W}; T_{mb} = 25\text{ °C}$	2.5	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink		0.3	K/W



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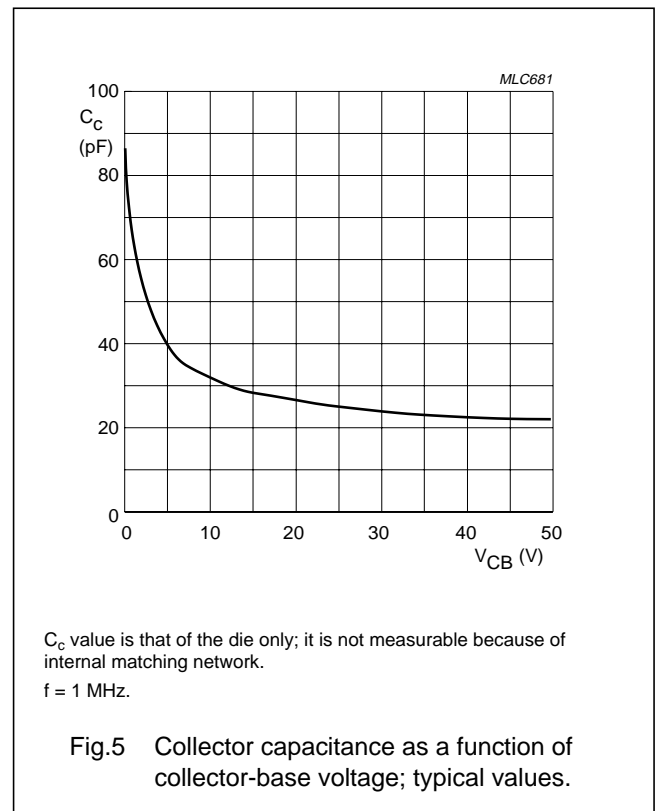
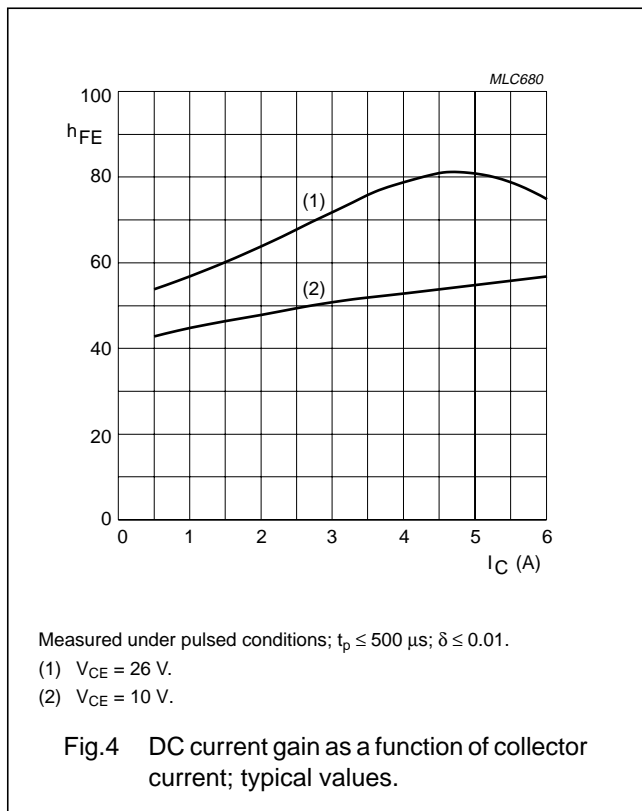
CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter; $I_C = 20\text{ mA}$	70	–	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	open base; $I_C = 50\text{ mA}$	30	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	open collector; $I_E = 1\text{ mA}$	3	–	–	V
I_{CES}	collector leakage current	$V_{BE} = 0$; $V_{CE} = 28\text{ V}$	–	–	2	mA
h_{FE}	DC current gain	$V_{CE} = 10\text{ V}$; $I_C = 1.5\text{ A}$; note 1	30	–	120	
C_c	collector capacitance	$V_{CB} = 26\text{ V}$; $I_E = i_e = 0$; $f = 1\text{ MHz}$; note 2	–	25	–	pF
C_{fe}	feedback capacitance	$V_{CE} = 26\text{ V}$; $I_C = 0$; $f = 1\text{ MHz}$	–	17	–	pF

Notes

1. Measured under pulsed conditions: $t_p \leq 500\text{ }\mu\text{s}$; $\delta \leq 0.01$.
2. C_c value is that of the die only; it is not measurable because of internal matching network.



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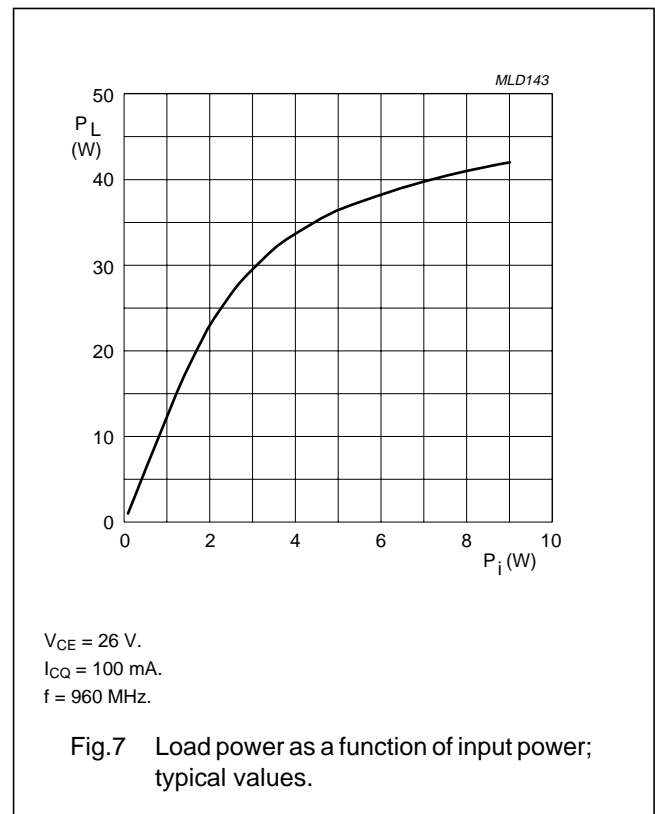
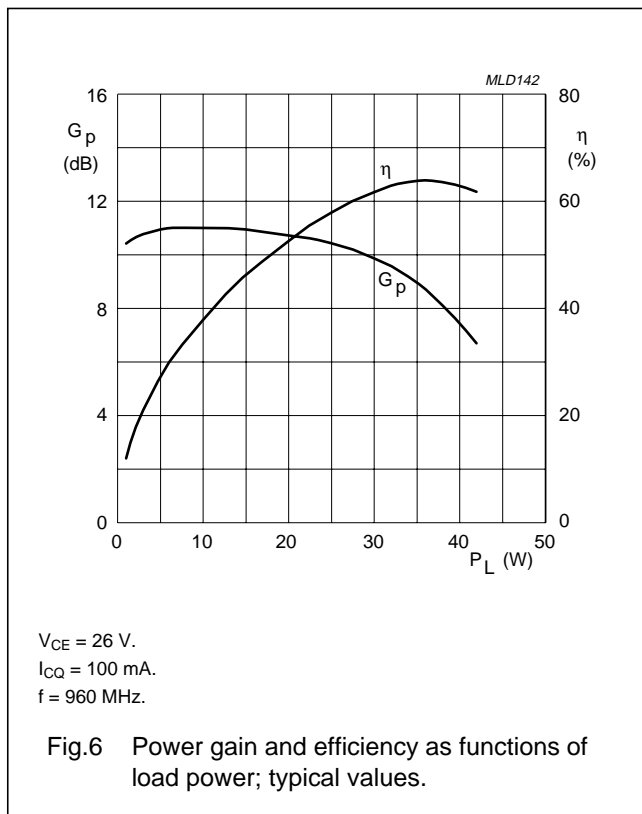
APPLICATION INFORMATION

RF performance at $T_h = 25\text{ }^\circ\text{C}$ in a common emitter, class-AB test circuit; $R_{th\text{ mb-h}} = 0.3\text{ K/W}$.

MODE OF OPERATION	f (MHz)	V _{CE} (V)	I _{CQ} (mA)	P _L (W)	G _p (dB)	η_c (%)
CW, class-AB	960	26	100	30	≥ 9 typ. 10	≥ 55 typ. 60

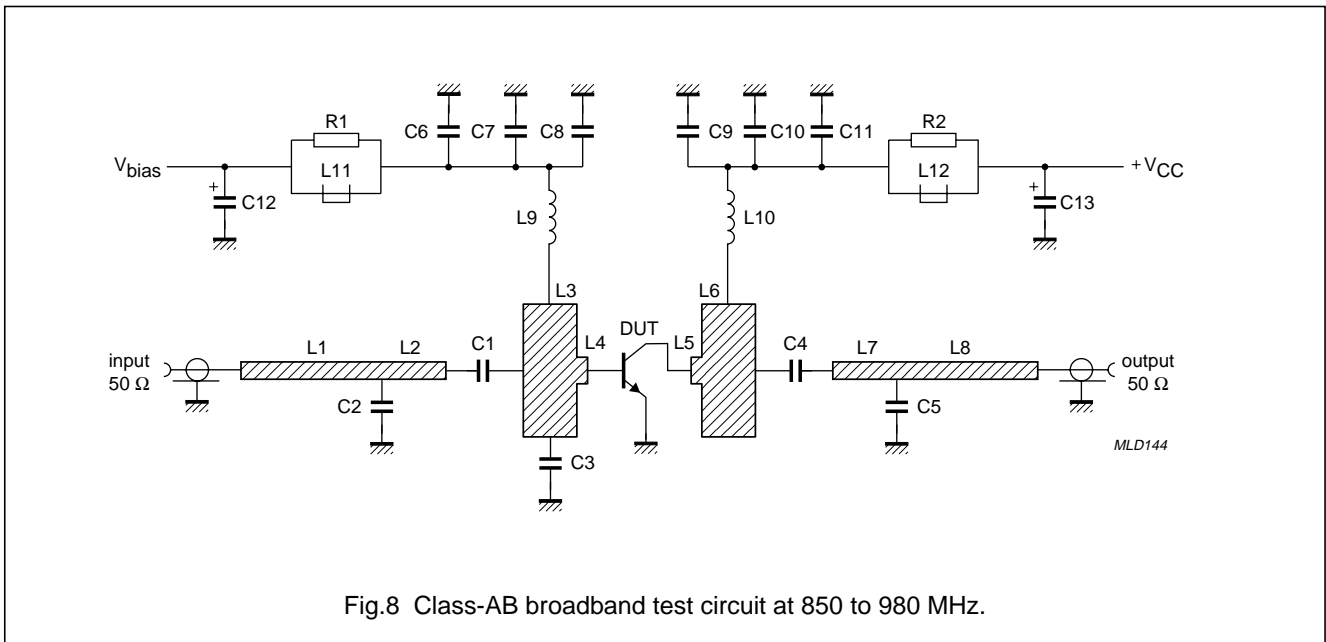
Ruggedness in class-AB operation

The BLV935 is capable of withstanding a load mismatch corresponding to $V_{SWR} = 5 : 1$ through all phases at rated output power, under the following conditions: $V_{CE} = 26\text{ V}$; $f = 960\text{ MHz}$; $I_{CQ} = 100\text{ mA}$; $T_h = 25\text{ }^\circ\text{C}$; $R_{th\text{ mb-h}} = 0.3\text{ K/W}$.



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List of components (see Figs 8 and 9)

COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE No.
C1, C4	multilayer ceramic chip capacitor; note 1	68 pF		
C2	multilayer ceramic chip capacitor; note 1	0.7 pF		
C3	multilayer ceramic chip capacitor; note 1	3.9 pF		
C5	multilayer ceramic chip capacitor; note 1	2 pF		
C6, C11	multilayer ceramic chip capacitor; note 1	1 nF		
C7, C8, C9, C10	multilayer ceramic chip capacitor; note 1	20 pF		
C12, C13	63 V solid aluminium capacitor	10 µF		2222 030 38109
L1, L8	stripline; note 2	50 Ω	41 × 2.4 mm	
L2, L7	stripline; note 2	50 Ω	12 × 2.4 mm	
L3, L6	stripline; note 2	9 Ω	10 × 20 mm	
L4, L5	stripline; note 2	38 Ω	4.5 × 3.5 mm	
L9	microchoke	100 nH		4322 057 01071

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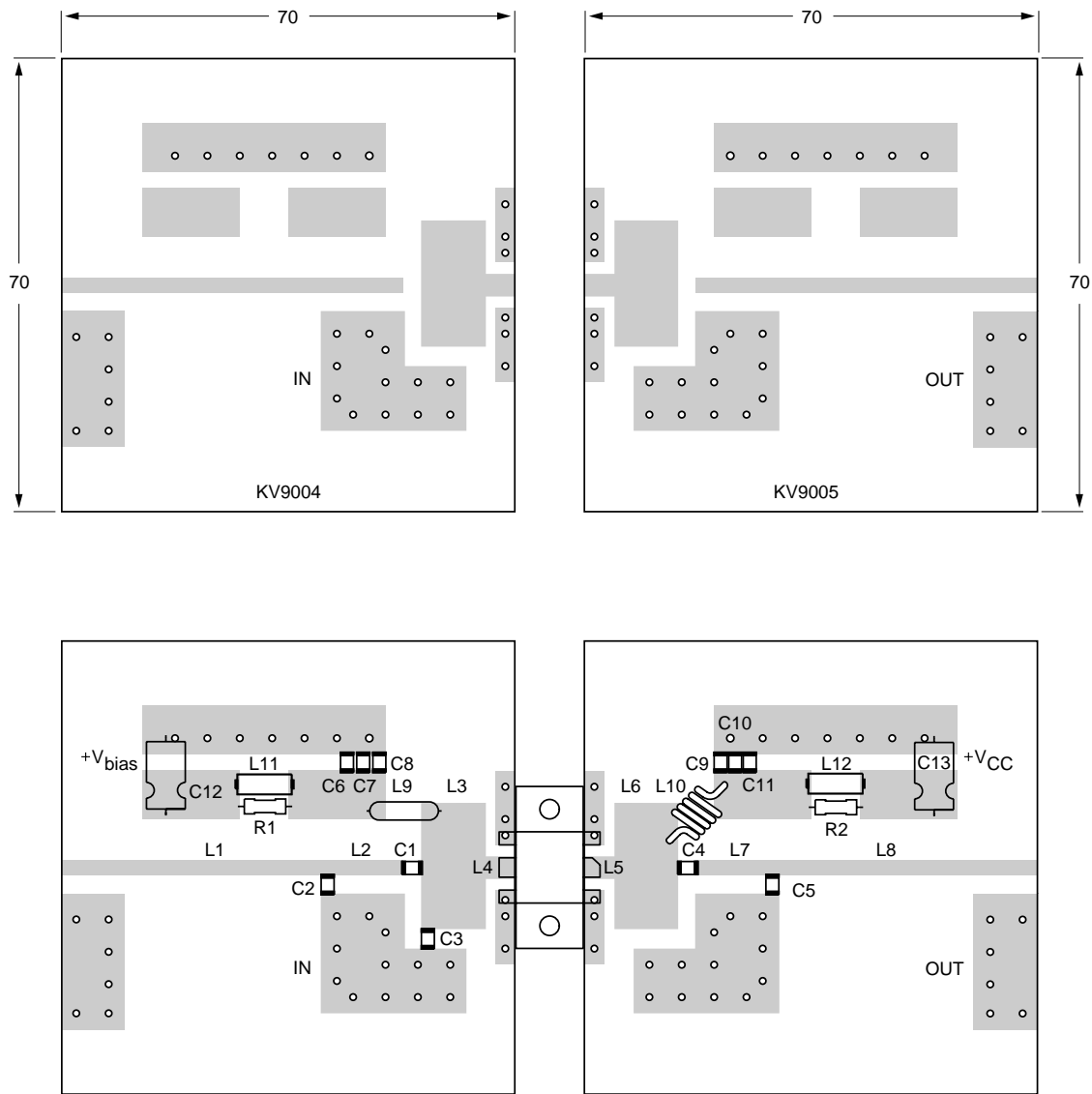
COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE No.
L10	4 turns 1 mm enamelled copper wire (close wound)	65 nH	internal diameter: 4 mm length: 4 mm leads: 2 × 5 mm	
L11, L12	grade 3B Ferroxcube wideband RF choke			4312 020 36642
R1, R2	metal film resistor	10 Ω ; 0.4 W		2322 151 71009

Notes

1. American Technical Ceramics type 100B or capacitor of same quality.
2. The striplines are on double-clad PCB with PTFE fibre-glass dielectric ($\epsilon_r = 2.2$); thickness $\frac{1}{32}$ ".

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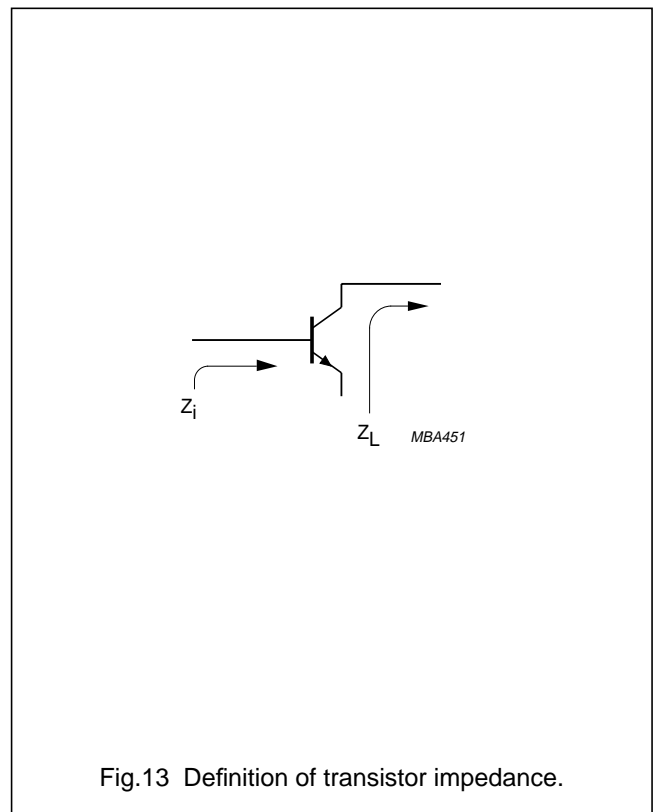
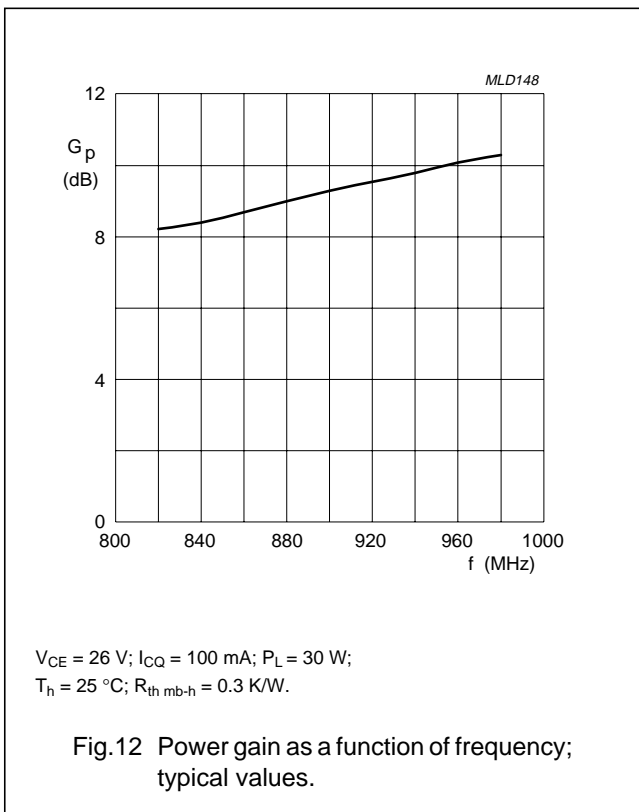
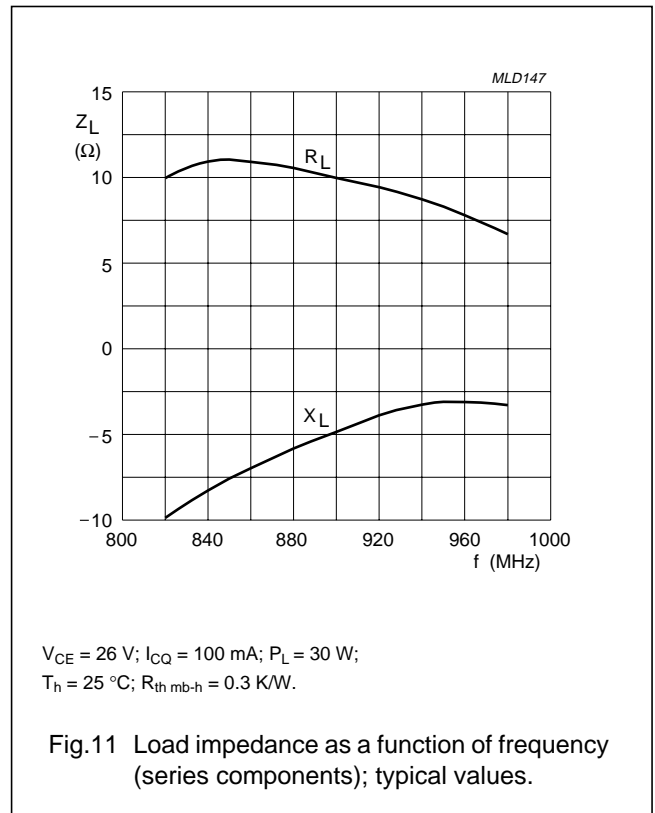
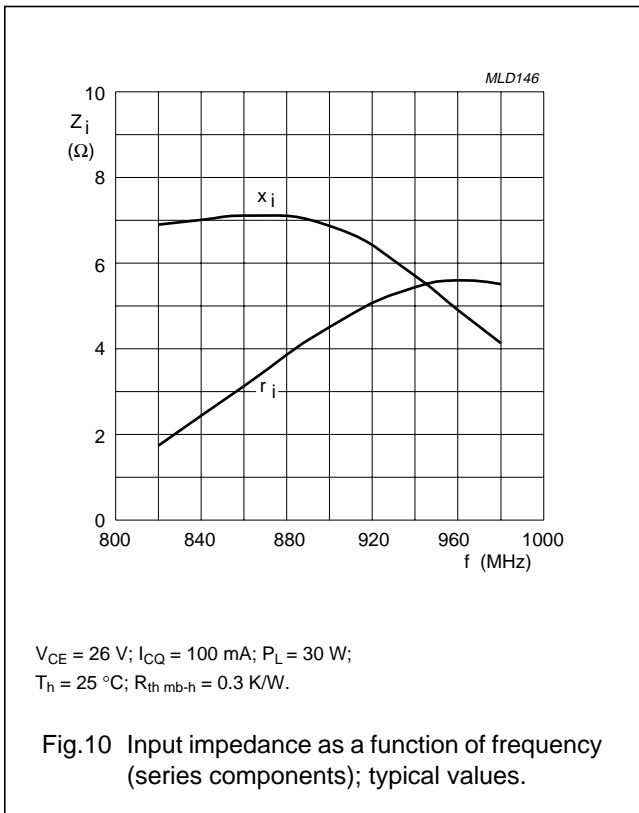
Dimensions in mm.

The components are located on one side of the PTFE fibre-glass board, the other side being fully metallized to serve as an earth. Earth connections are made by fixing screws, hollow rivets and copper straps around the board and under the emitters to provide a direct contact between the component side and the ground plane.

Fig.9 Printed circuit board and component layout for class-AB test circuit (850-980 MHz).

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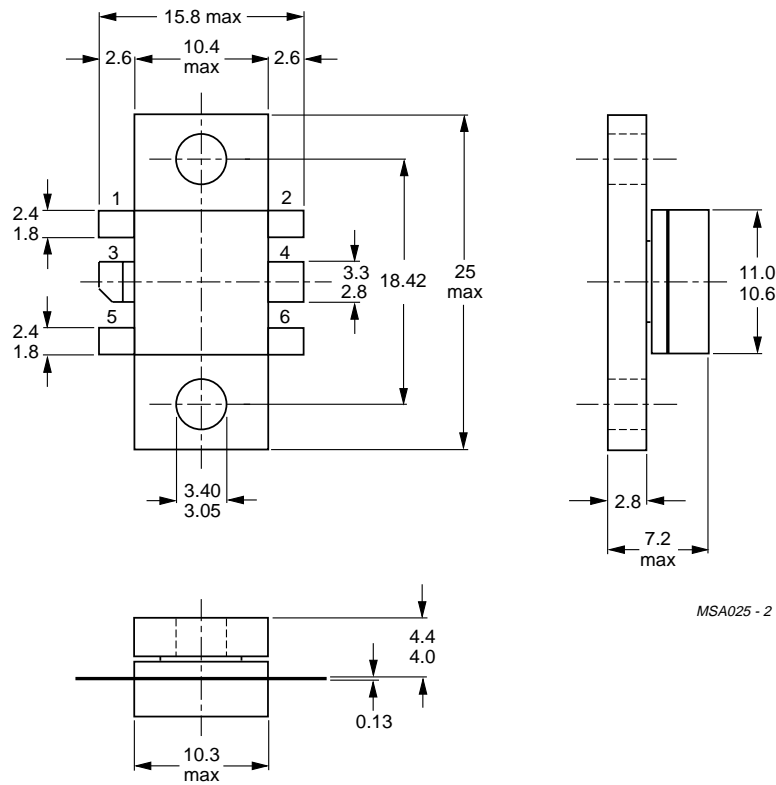
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PACKAGE OUTLINE



Dimensions in mm.

Torque on screw: min. 0.6 Nm; max. 0.75 Nm.

Recommended screw: cheese-head 4-40 UNC/2A.

Heatsink compound must be applied sparingly and evenly distributed.

Fig.14 SOT273.

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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